

# C0805C223K5HACTU

Aliases (C0805C223K5HAC7800)

SMD Comm X8R HT150C, Ceramic, 0.022 uF, 10%, 50 VDC, X8R, SMD, MLCC, High Temperature, Ultra-Stable, 0805, 0.7 mm



General Information		
Series	SMD Comm X8R HT150C	
Style	SMD Chip	
Description	SMD, MLCC, High Temperature, Ultra-Stable	
Features	High Temperature, Ultra-Stable	
RoHS	Yes	
Termination	Tin	
Marking	No	
AEC-Q200	No	
Typical Component Weight	21 mg	
Shelf Life	78 Weeks	
MSL	1	

Dimensions	
Chip Size	0805
L	2mm +/-0.2mm
W	1.25mm +/-0.2mm
Т	1.1mm +/-0.10mm
S	0.7mm MIN
В	0.5mm +/-0.25mm

W	1.25mm +/-0.2mm	Tolerance	10%
Т	1.1mm +/-0.10mm	Voltage DC	50 VDC
S	0.7mm MIN	Dielectric Withstanding Voltage	125 VDC
В	0.5mm +/-0.25mm	Temperature Range	-55/+150°C
		Temp. Coefficient	X8R
Packaging Specifications		Capacitance Change with	15%, 1kHz 1.0Vrms
Packaging	T&R, 180mm, Plastic Tape	Reference to +25°C and 0 VDC Applied (TCC)	
Packaging Quantity 2500	Dissipation Factor	2.5%1kHz1.0Vrms	
		Aging Rate	0% Loss/Decade Hour: Referee

Specifications		
Capacitance	0.022 uF	
Measurement Condition	1 kHz 1.0Vrms	
Tolerance	10%	
Voltage DC	50 VDC	
Dielectric Withstanding Voltage	125 VDC	
Temperature Range	-55/+150°C	
Temp. Coefficient	X8R	
Capacitance Change with Reference to +25°C and 0 VDC Applied (TCC)	15%, 1kHz 1.0Vrms	
Dissipation Factor	2.5% 1 kHz 1.0Vrms	
Aging Rate	0% Loss/Decade Hour: Referee Time is 1000 Hours	
Insulation Resistance	45.4545 GOhms	

Statements of suitability for certain applications are based on our knowledge of typical operating conditions for such applications, but are not intended to constitute - and we specifically disclaim - any warranty concerning suitability for a specific customer application or use. This Information is intended for use only by customers who have the requisite experience and capability to determine the correct products for their application. Any technical advice inferred from this Information or otherwise provided by us with reference to the use of our products is given gratis, and we assume no obligation or liability for the advice given or results obtained.

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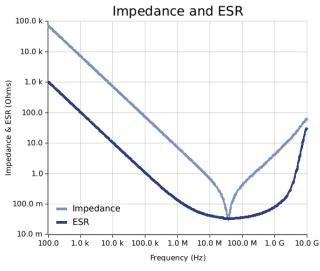


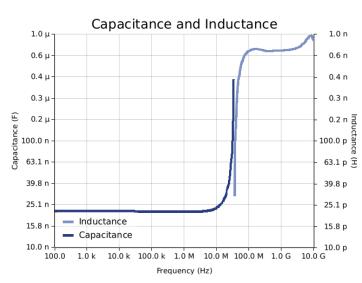
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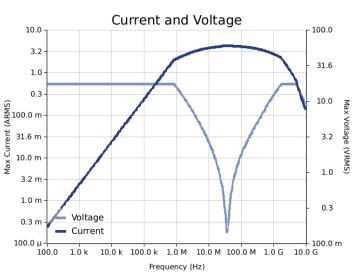
Aliases (C0805C223K5HAC7800) SMD Comm X8R HT150C, Ceramic, 0.022 uF, 10%, 50 VDC, X8R, SMD, MLCC, High Temperature, Ultra-Stable, 0805, 0.7 mm

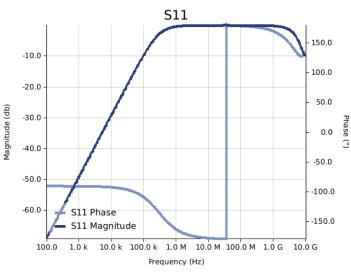
### **Simulations**

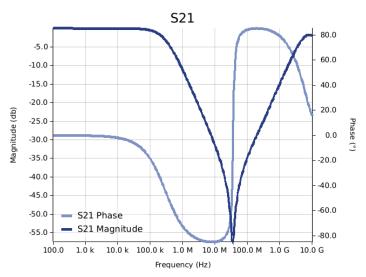
For the complete simulation environment please visit K-SIM.











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#### These are simulations.

This is not a specification!

The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

The responses shown do not represent a specified or implied maximum capability of the device for all applications.

- The ESR used for ripple "Ripple Current/Voltage vs. Frequency" plots is the ESR at ambient temperature.

- The ESR used for ripple Ripple Currenty votage vs. rrequency plots is unleast at an interact temperature.
  The ESR in the "Temperature Rise vs. Ripple Current" plots is adjusted to each incremental temperature rise before the power and ripple current is calculated.
  The effects shown herein are based on measured data from a multiple part sample of the parts in question.
  Ripple capability of this device will be factored by thermal resistance (Rth) created by circuit traces (addi affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.
  The peak voltages generated in the "Temperature Rise vs. Combined Ripple Currents" plot are calculated for each frequency and are not combined with voltages
- generated at any other harmonics.

  Please consult with the catalog or field applications engineer for maximum capability of the device in specific applications.

All product information and data (collectively, the "Information") are subject to change without notice.

KEMET K-SIM is designed to simulate behavior of components with respect to frequency, ambient temperature, and DC bias levels. The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation effects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

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If you have any questions please contact K-SIM.

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